



RESEARCH ARTICLE

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MATHEMATICAL MODELING OF STATIONARY TEMPERATURE FIELDS FOR CONSTRUCTION OF MICROELECTRONIC DEVICES

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ABSTRACT

The problem of analyzing stationary temperature fields in the form of a parallelepiped is under consideration. Heat sources are located on the top of the parallelepiped. The path to the solution of the problem starts from the basic equation of thermal conductivity which is mathematically described with the Laplace equation system.

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I. INTRODUCTION

The mathematical model for a multilayer rectangular parallelepiped with the layers of the same size is solved on the basis of physically justified boundary conditions. An algorithm is proposed for calculating the temperature at each point of the examined structure.

II. DESCRIPTION OF THE PROBLEM

$$\frac{\partial^2 T^{(j)}(x,y,z)}{\partial x^2} + \frac{\partial^2 T^{(j)}(x,y,z)}{\partial y^2} + \frac{\partial^2 T^{(j)}(x,y,z)}{\partial z^2} = 0 \tag{1}$$

III. ANALYSIS

The analysis is carried out under the following boundary conditions:

$$\frac{\partial T^{(j)}(L_x,y,z)}{\partial x} = 0, \frac{\partial T^{(j)}(x,L_y,z)}{\partial y} = 0, \frac{\partial T^{(j)}(x,y,z)}{\partial x} = 0, \frac{\partial T^{(j)}(x,y,0)}{\partial y} = 0, \tag{2}$$

where $j = 1, 2, 3, \dots, N$ - the number of layers in the parallelepiped.

For the first layer the following boundary conditions are fulfilled:

$$-\lambda^{(i)} \frac{\partial T^{(i)}}{\partial z} + \alpha(T^{(i)} - T_0) = Q(x,y), \text{ for } z = 0, \tag{3}$$

$$Q(x, y) = \begin{cases} \frac{P_i}{l_{x_i} l_{y_i}}; (x_i, y_i) \in D_i \\ 0, (x_i, y_i) \notin D_i. \end{cases}$$

where D_i the domain of the i -th element, l_{x_i} and l_{y_i} the dimensions of i -th source of heat, $i = 1, 2, \dots, n_1$; n_1 – number of heat sources, P_i – power dissipated by i -th source; α – coefficient of heat exchange with the environment; $\lambda^{(j)}$ – coefficient of the j -th layer; T_0 – temperature of the environment; $Q(x, y)$ – density function of the heat flow. Let $T_0 = 0$.

In order to ensure the continuity of the heat flow between the layers we introduce the following necessary conditions:

$$T^{(j)}(x, y, z_j) = T^{(j+1)}(x, y, z_j), \tag{4}$$

$$\lambda^{(j)} \frac{\partial T^{(j)}(x, y, z_j)}{\partial z} = \lambda^{(j+1)} \frac{\partial T^{(j+1)}(x, y, z_j)}{\partial z}, \tag{5}$$

$$T^{(N)}(x, y, z_N) = T_b; (x, y) \in D_L. \tag{6}$$

where:

- D_L is the domain of the base of parallelepiped;
- L_x and L_y – dimensions of the base;
- $T_k = \text{const}$;
- $z_N = \sum_{j=1}^N h_j$ – the base points.

IV. SOLUTION

The solution of the problem (1) with the method of Fourier in general form is presented in the form:

$$T(x, y, z) = Z(z) \cdot V(x, y) = Z(z) X(x) Y(y),$$

$$X_n^{(j)}(x) = D_n^{(j)} \cdot \cos \frac{n\pi x}{L_x}; Y_m^{(j)}(y) = F_m^{(j)} \cdot \cos \frac{m\pi y}{L_y};$$

$$Z_{nm}^{(j)}(z - z_{j-1}) = H_{nm}^{(j)} \operatorname{sh} \gamma_{nm} (z - z_{j-1}) + G_{nm}^{(j)} \operatorname{ch} \gamma_{nm} (z - z_{j-1}), \tag{7}$$

$$\gamma_{nm} = \pi \sqrt{\frac{n^2}{L_x^2} + \frac{m^2}{L_y^2}}, n = 1, 2, 3, \dots, m = 1, 2, 3, \dots,$$

where n and m are the indexes of the terms of the series; $D_n^{(j)}, F_m^{(j)}, H_{nm}^{(j)}, G_{nm}^{(j)}$ are indeterminate constants.

The general solution of the distribution of the temperature field in each layer of the structure with boundary conditions (2)-(6) is assumed in the form:

$$T^{(j)} = \sum_{n=1}^{\infty} \sum_{m=1}^{\infty} X_n^{(j)}(x) Y_m^{(j)}(y) Z_{nm}^{(j)}(z)$$

Substituting the expressions from (7) in the last equality, grouping the indeterminate constants and we get the solution in the form:

$$T^{(j)}(x, y, z - z_{j-1}) = G_{00}^{(j)} + H_{00}^{(j)}(z - z_{j-1}) +$$

$$+ \sum_{n=1}^{\infty} \left[H_{n0}^{(j)} \operatorname{sh} \frac{n\pi(z-z_{j-1})}{L_x} + G_{n0}^{(j)} \operatorname{ch} \frac{n\pi(z-z_{j-1})}{L_x} \right] \cos \frac{n\pi x}{L_x} +$$

$$+ \sum_{m=1}^{\infty} \left[H_{0m}^{(j)} \operatorname{sh} \frac{m\pi(z-z_{j-1})}{L_y} + G_{0m}^{(j)} \operatorname{ch} \frac{m\pi(z-z_{j-1})}{L_y} \right] \cos \frac{m\pi y}{L_y} +$$

$$+ \sum_{n=1}^{\infty} \sum_{m=1}^{\infty} \left[H_{nm}^{(j)} \operatorname{sh} \gamma_{nm} (z - z_{j-1}) + G_{nm}^{(j)} \operatorname{ch} \gamma_{nm} (z - z_{j-1}) \right] \cos \frac{n\pi x}{L_x} \cos \frac{m\pi y}{L_y}. \tag{8}$$

1. Calculate the coefficients A_{n0} , A_{0m} and A_{nm} using the above formulas.
2. From the system (10) we have:

$$\begin{cases} G_{nm}^{(N)} = \left(\frac{-c_N}{b_N} \right) H_{nm}^{(N)} = d_N H_{nm}^{(N)} \\ H_{nm}^{(N)} = 1 \cdot H_{nm} = l_N H_{nm} \end{cases}$$

$$\begin{cases} G_{nm}^{(N-1)} = \left(\frac{-b_{N-1} \cdot c_N}{b_N} - \frac{\lambda_N}{\lambda_{N-1}} \cdot c_{N-1} \right) H_{nm}^{(N)} = d_{N-1} H_{nm}^{(N)} \\ H_{nm}^{(N-1)} = \left(\frac{c_{N-1} c_N}{b_N} + \frac{\lambda_N}{\lambda_{N-1}} \cdot b_{N-1} \right) \cdot H_{nm}^{(N)} = l_{N-1} H_{nm}^{(N)} \end{cases}$$

The recurrent dependence for $G_{nm}^{(j)}$ and $H_{nm}^{(j)}$ is:

$$\begin{cases} G_{nm}^{(j)} = \left(b_j \cdot d_{j+1} - \frac{\lambda_{j+1}}{\lambda_j} \cdot c_j \cdot l_{j+1} \right) H_{nm}^{(N)} = d_j H_{nm}^{(N)} \\ H_{nm}^{(j)} = \left(-c_j d_{j+1} + \frac{\lambda_{j+1}}{\lambda_j} \cdot b_j \cdot l_{j+1} \right) \cdot H_{nm}^{(N)} = l_j H_{nm}^{(N)} \end{cases} \tag{11}$$

From (11) we determine d_j and l_j for $j = N - 2, N - 3, \dots, 1$. Then:

$$\begin{cases} H_{nm}^{(N)} = \frac{A_{nm}}{\alpha d_1 - \lambda^{(1)} \gamma_{nm} \cdot l_1} \\ G_{nm}^{(N)} = d_N \cdot H_{nm}^{(N)} \end{cases}$$

$$\begin{cases} G_{nm}^{(j)} = d_j H_{nm}^{(N)} \\ H_{nm}^{(j)} = l_j \cdot H_{nm}^{(N)} \end{cases} \quad j = 1, 2, \dots, N - 1$$

Since

$$\begin{cases} b_j = ch(\gamma_{nm} \cdot h_j) \\ c_j = sh(\gamma_{nm} \cdot h_j) \end{cases} \quad j = 1, 2, \dots, N.$$

Using the above formulas finite number of coefficients $H_{nm}^{(j)}$ and $G_{nm}^{(j)}$ are calculated.

3. Substitute the coefficients $H_{nm}^{(j)}$ and $G_{nm}^{(j)}$ in series (8). The sum of the known addends of this series represents an approximate temperature value at any point of the multilayer structure.

V. RESUME

The temperature value of any point of the multilayer structure can be used to design the structure of microelectronic devices.

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